



## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

NMOS(Die1/Die2)

$V_{DS}$

40V

$I_D$



# YJGD60G04HJQ

RECOMMEND  
[YJGD60G04HHQ](#)  
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## Ordering Information (Example)

PREFERED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJGD60G04HJQ	F1					



Typical Electrical and Thermal Characteristics Diagrams

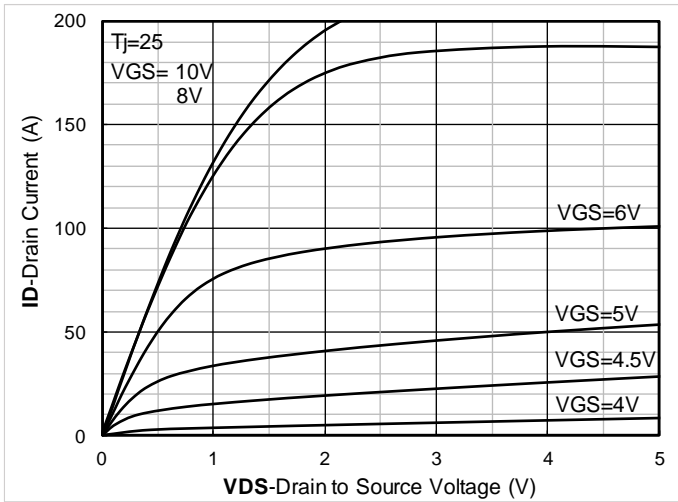


Figure 1. Output Characteristics



Figure 2. Transfer Characteristics

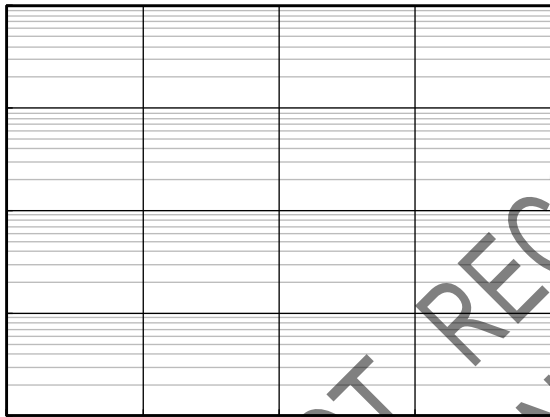


Figure 3. Capacitance Characteristics

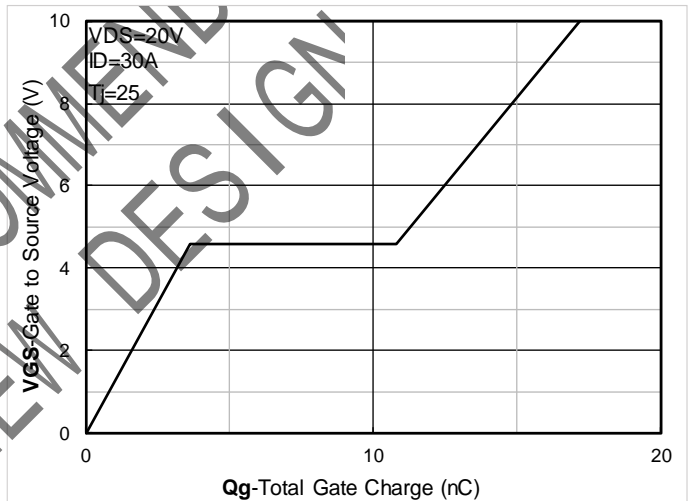


Figure 4. Gate Charge

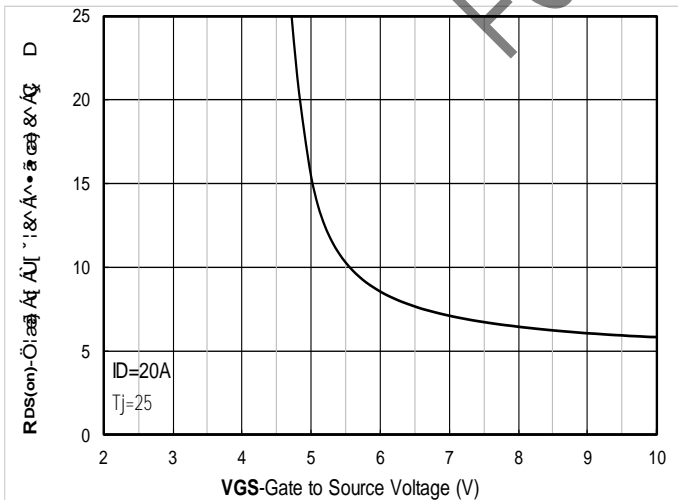


Figure 5. On-Resistance vs Gate to Source Voltage

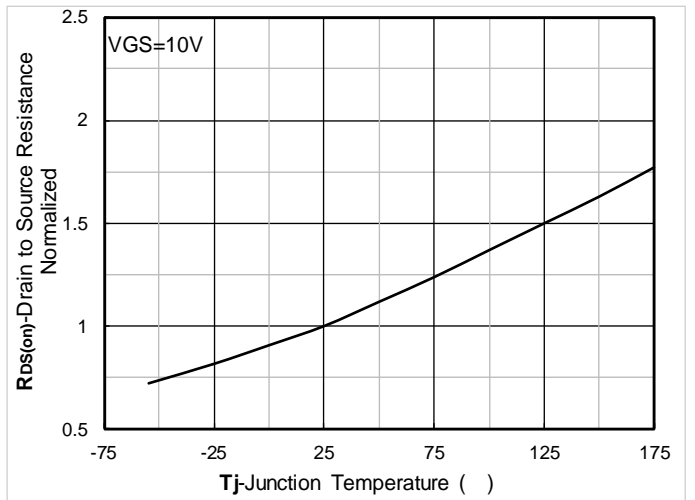


Figure 6. Normalized On-Resistance

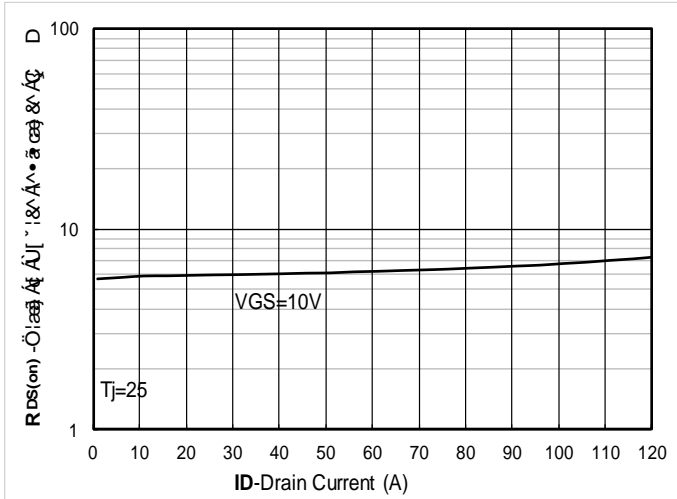


Figure 7.  $R_{DS(on)}$  VS Drain Current

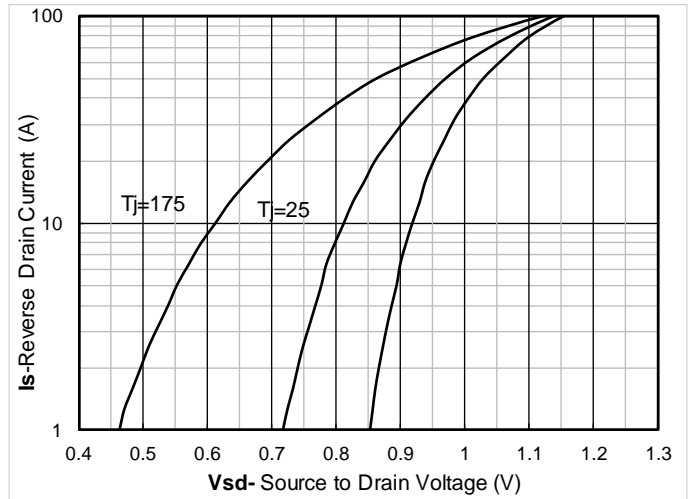


Figure 8. Forward characteristics of reverse diode

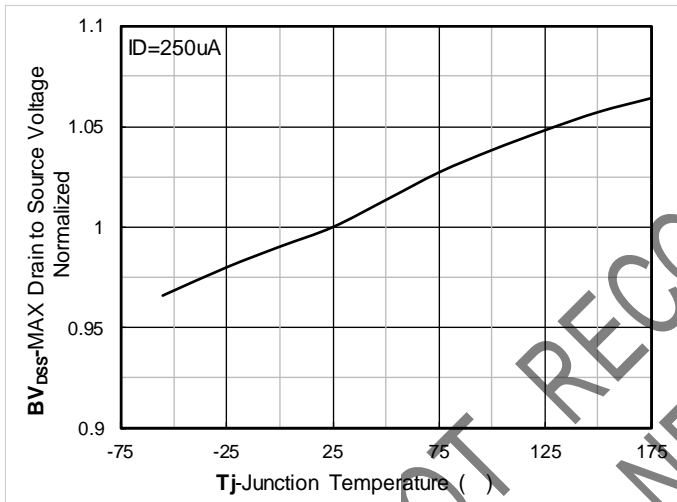


Figure 9. Normalized breakdown voltage

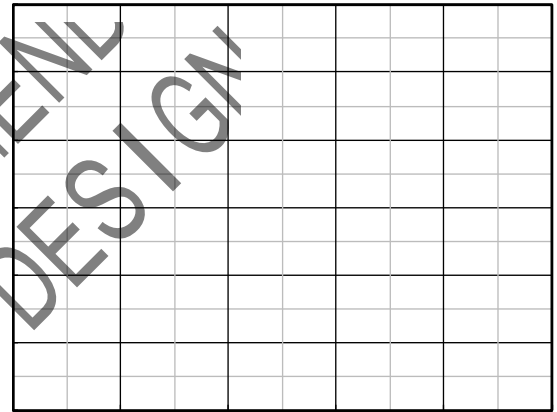


Figure 10. Normalized Threshold voltage

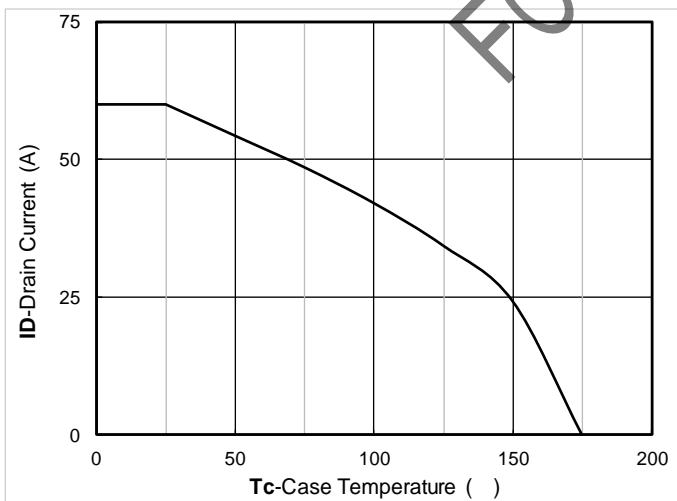


Figure 11. Current dissipation

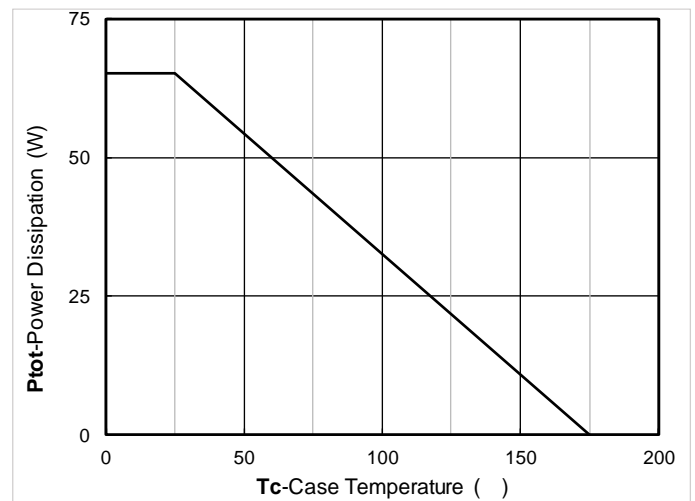


Figure 12. Power dissipation

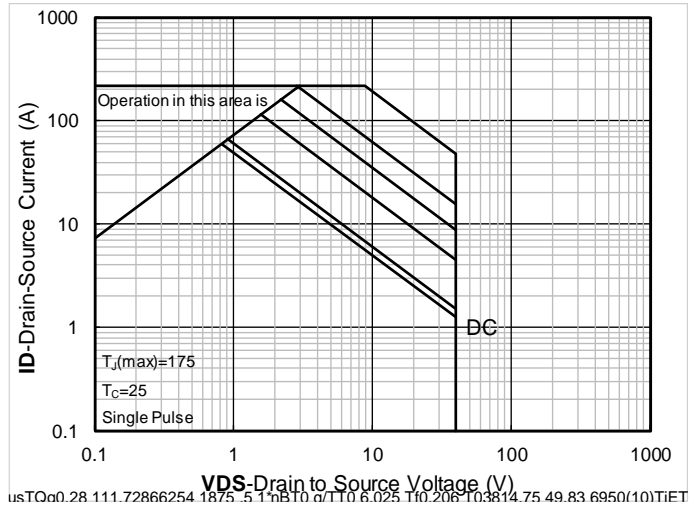


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

NOT RECOMMEND  
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Disc